

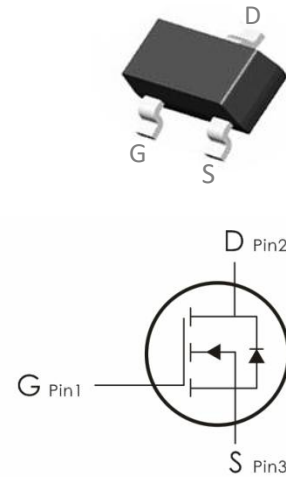
SDescription:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=4.8A, R_{DS(ON)} < 35m\Omega @ V_{GS}=10V$ (Typ: $27m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DO3400E	A09T	SOT-23	3000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current ¹	4.8	A
	Continuous Drain Current- $T_A=100^\circ\text{C}$ ¹	3.4	
I_{DM}	Pulsed Drain Current ²	19.2	
P_D	Power Dissipation	1.24	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	101	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=30V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	0.5	0.85	1.3	V
$R_{DS(on)}$	Drain-Source On Resistance ³	$V_{GS}=10V, I_D=3.6A$	---	27	35	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=3A$	---	30	39	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=500\text{KHz}$	---	521	---	pF
C_{oss}	Output Capacitance		---	42	--	
C_{rss}	Reverse Transfer Capacitance		---	33	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V, I_D=4A,$ $R_{ENG}=3\ \Omega, V_{GS}=10V$	---	7	---	ns
t_r	Rise Time		---	2	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	17	---	ns
t_f	Fall Time		---	2	---	ns
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=24V,$ $I_D=4A$	---	12	---	nC
Q_{gs}	Gate-Source Charge		---	1	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=4A$	---	---	1	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	4.8	A
I_{SM}	Pulsed Drain Current		---	---	19.2	A
T_{rr}	Reverse Recovery Time	$I_F=4A, T_J=25^{\circ}\text{C}$	---	13	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu\text{s}$	---	0.01	---	μC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_A=25^\circ C$ unless otherwise noted)

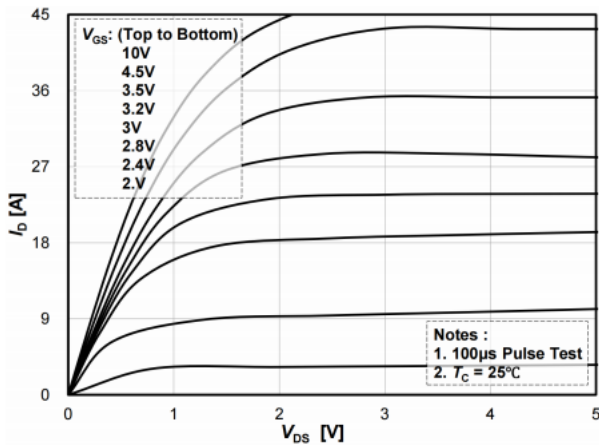


Figure 1. On-Region Characteristics

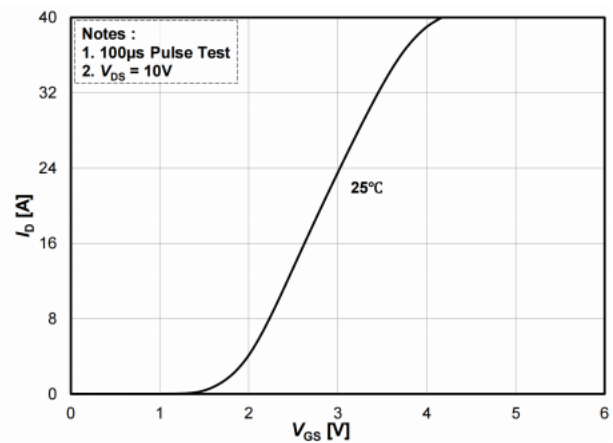


Figure 2. Transfer Characteristics

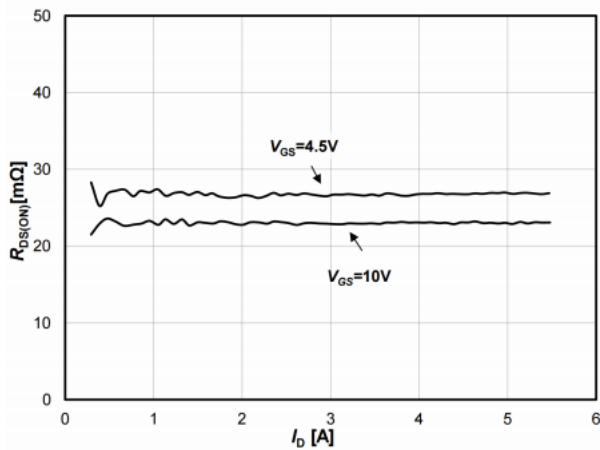


Figure 3. On Resistance vs. Drain Current

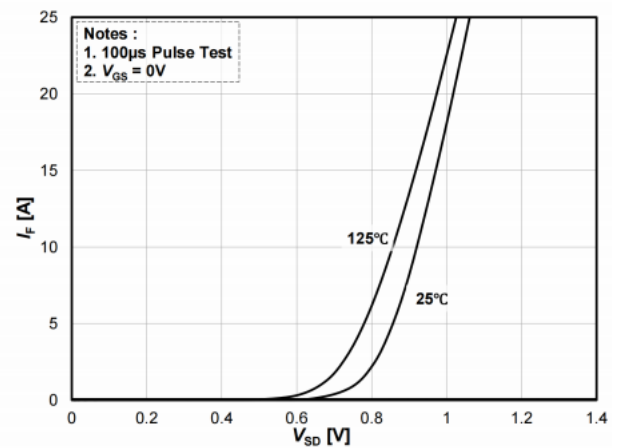


Figure 4. Diode Forward Voltage vs. Current

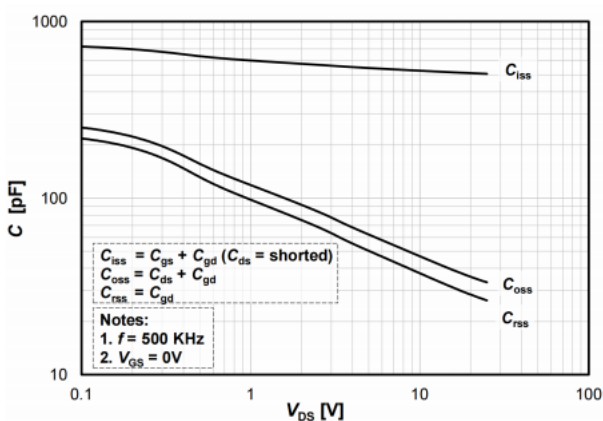


Figure 5. Capacitance Characteristics

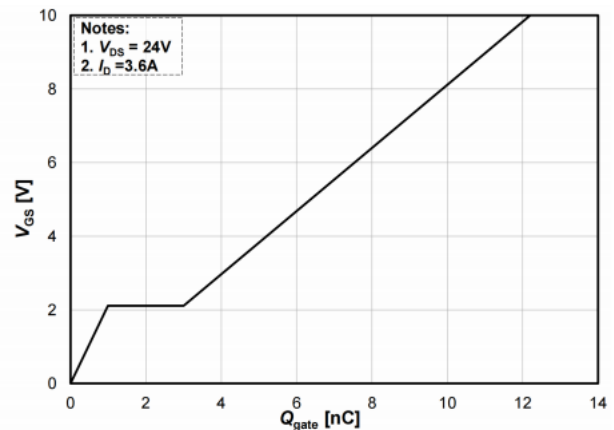


Figure 6. Gate Charge Characteristics

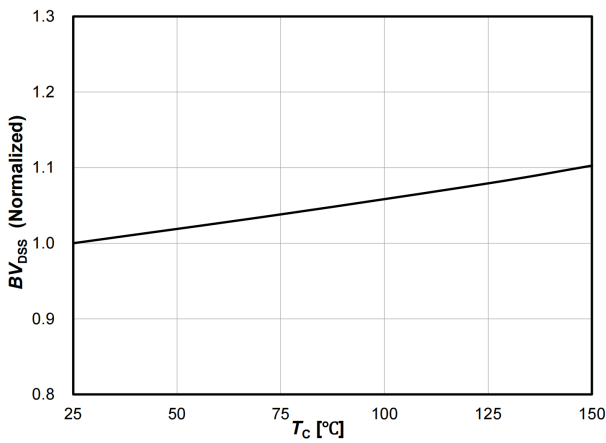


Figure 7. Normalized BV_{DSS} vs. Temperature

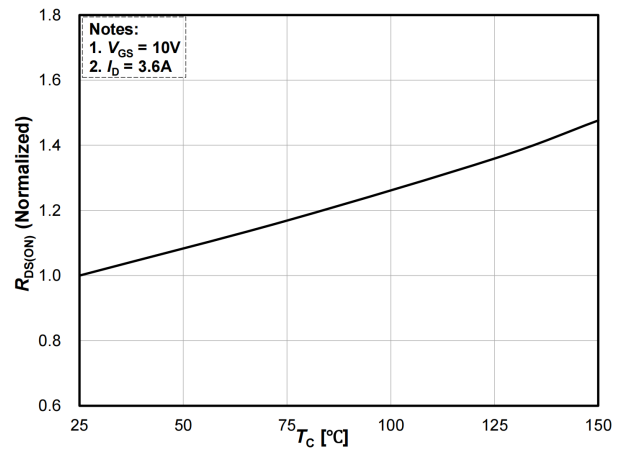


Figure 8. Normalized On-Resistance Variation vs. Temperature

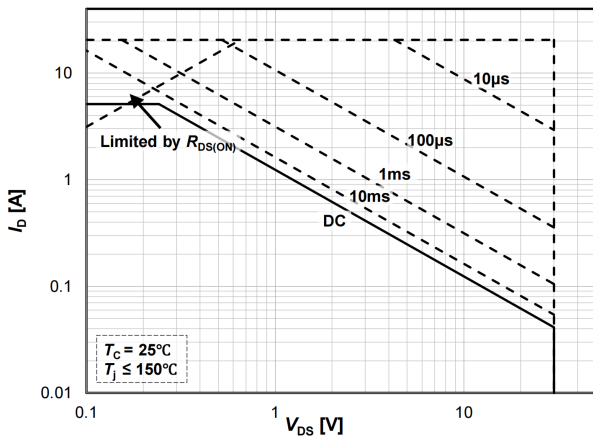


Figure 9. Safe Operating Area ³⁾

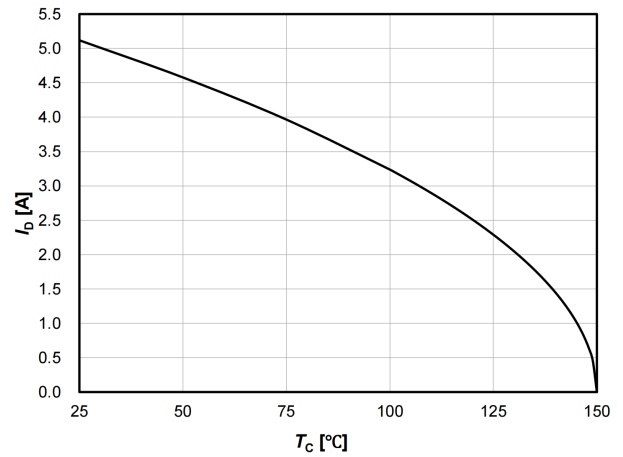


Figure 10. Drain Current vs. Temperature

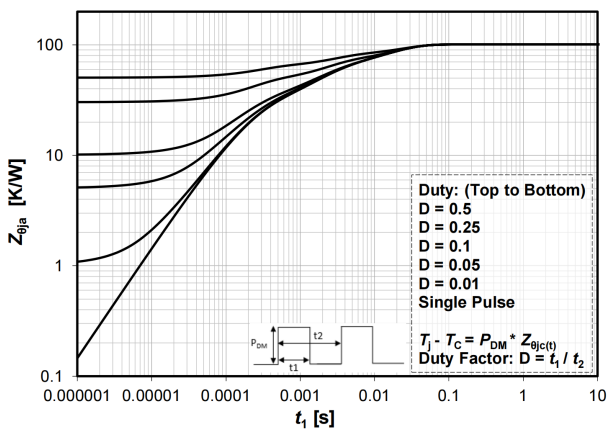
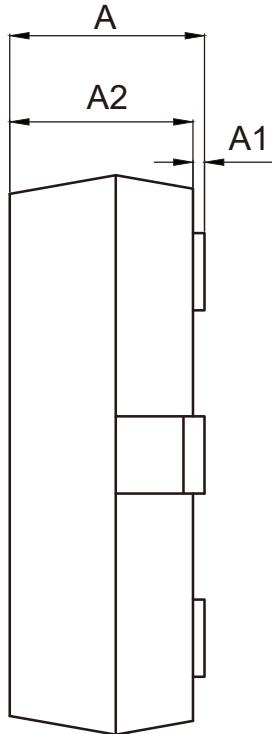
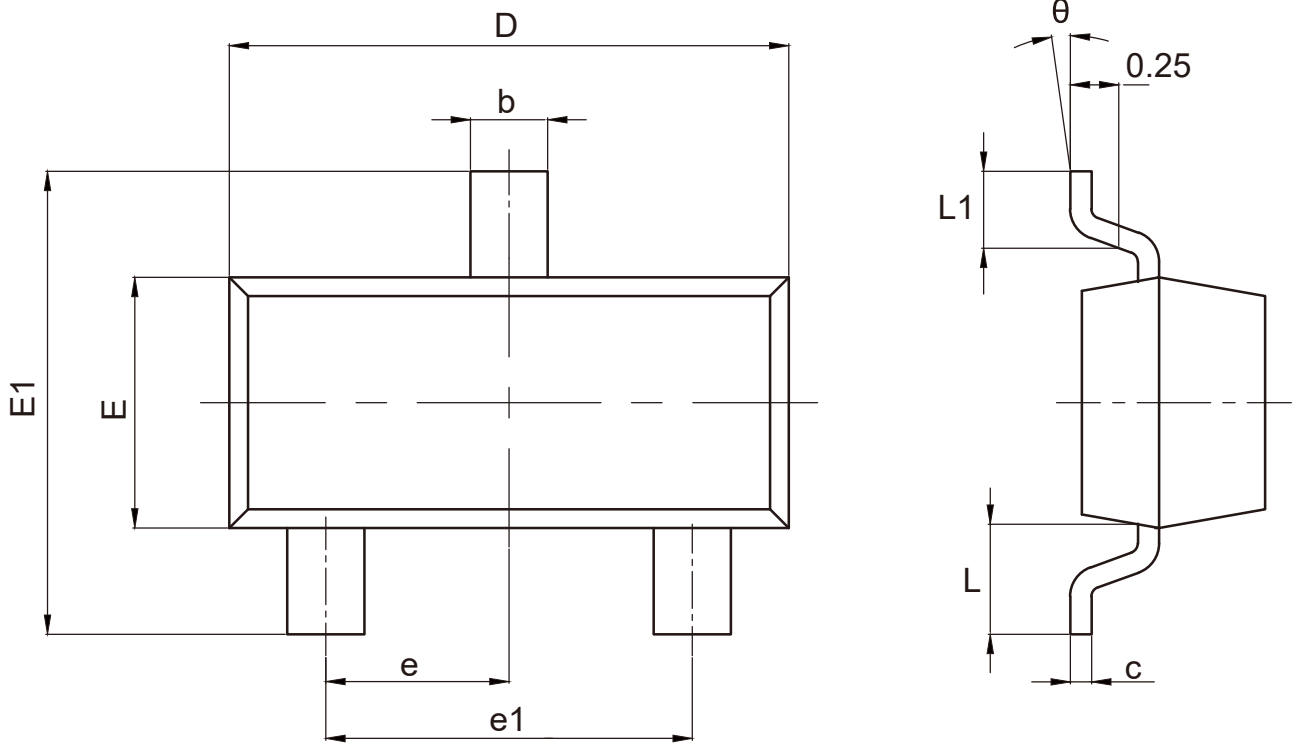


Figure 11. Transient Thermal Impedance

SOT-23 Package Outline Data

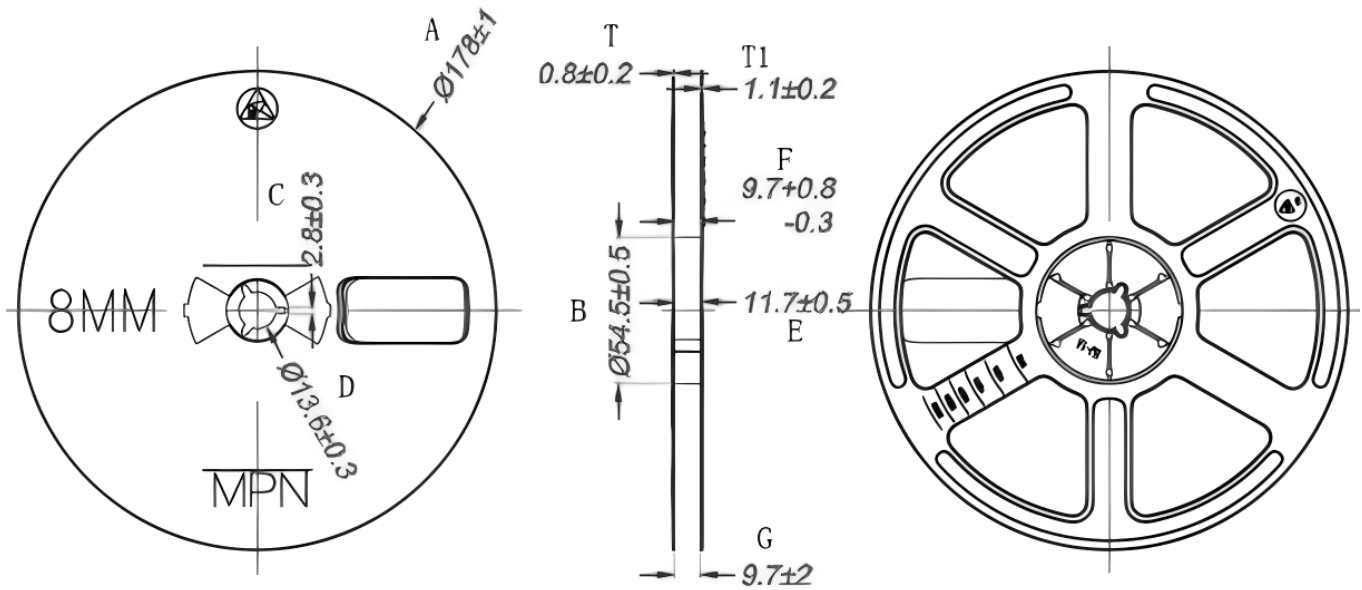


COMMON DIMENSIONS			
CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	0.900	--	1.150
A1	0.000	--	0.100
A2	0.900	--	1.050
c	0.100	--	0.200
b	0.300	0.400	0.500
D	2.800	2.900	3.000
E	1.200	--	1.400
E1	2.250	--	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.550REF		
L1	0.300	0.400	0.500
θ	0°	--	8°

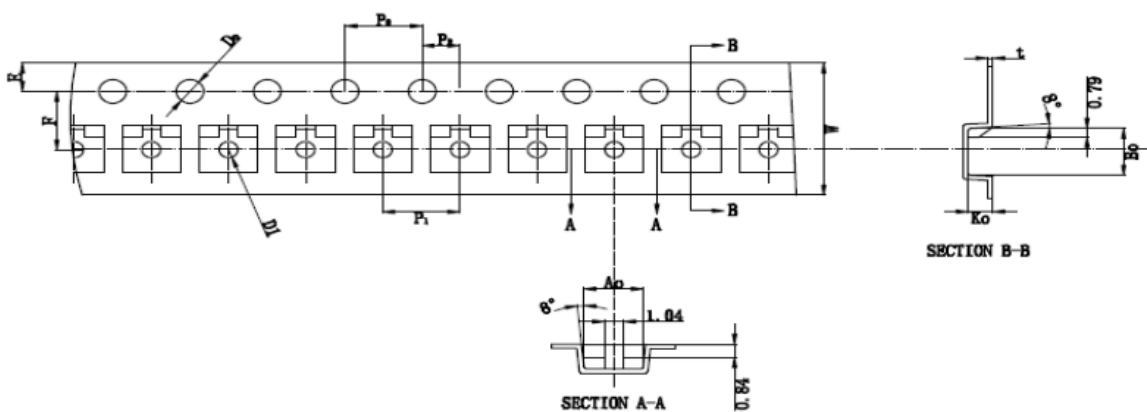
Unit:mm

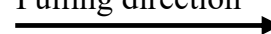
Tape & Reel Information

Dimensions in mm

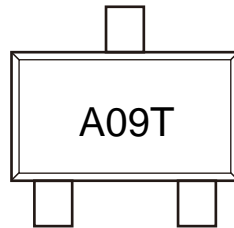


PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT-23	8.00	4.00	1.75	3.50	1.55	1.00	4.00	40.00	2.00	3.17	2.77	1.28	0.20
Tolerance	+0.3/-0.1	± 0.1	± 0.1	± 0.05	± 0.1	± 0.1	± 0.1	± 0.2	± 0.05	± 0.1	± 0.1	± 0.1	± 0.03



Pulling direction 


Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
1.1	2025-11-14	Release of final version

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